

MSC2X51_50DC70J SiC Diode Power Module

1 Product Overview

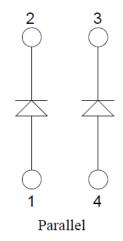
This section shows the product overview of the MSC2X51_50DC70J device.



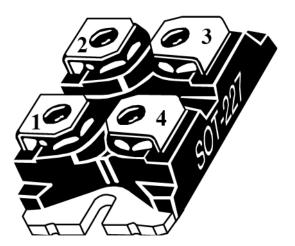


Anti-Parallel

MSC2X50DC70J



MSC2X51DC70J



All ratings at T_j = 25°C, unless otherwise specified.

Caution: These devices are sensitive to electrostatic discharge. Proper handling procedures should be followed.



1.1 Features

The following are the key features of the MSC2X51_50DC70J device:

- Silicon carbide (SiC) Schottky diode
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature-independent switching behavior
 - Positive temperature coefficient on VF
- Very low stray inductance

1.2 Benefits

The following are the benefits of the MSC2X51 50DC70J device:

- Outstanding performance at high-frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- RoHS compliant

1.3 Applications

The MSC2X51_50DC70J device is designed for the following applications:

- Uninterruptible power supplies
- Induction heating
- Welding equipment
- High-speed rectifiers



2 Electrical Specifications

This section shows the electrical specifications of the MSC2X51_50DC70J device.

2.1 Absolute Maximum Ratings

The following table shows the absolute maximum ratings per SiC diode of the MSC2X51_50DC70J device.

Table 1 • Absolute Maximum Ratings

Symbol	Parameter		Maximum Ratings	Unit
Vrrm	Repetitive peak reverse voltage		700	V
IF	DC forward current	Tc = 80 °C	50	А

The following table shows the thermal and package characteristics of the MSC2X51_50DC70J.

Table 2 • Thermal and Package Characteristics

Symbol	Characteristic	Min	Тур	Max	Unit
VISOL	RMS isolation voltage, any terminal to case t =1 minute, 50 Hz/60 Hz	2500			V
TJ, Tstg	Storage temperature range	-55		175	°C
TJOP	Recommended junction temperature under switching conditions	-55		T _{Jmax} – 25	-
Torque	Terminals and mounting screws			1.1	N.m
Wt	Package weight		29.2		g

2.2 Electrical Performance

The following table shows the electrical characteristics per SiC diode of the MSC2X51_50DC70J.

Table 3 • Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
VF	Diode forward voltage	IF = 50 A	T _j = 25 °C		1.5	1.8	V
			T _j = 175 °C		1.9		-
Irm	Reverse leakage current	V _R = 700 V	T _j = 25 °C		15	200	μΑ
			T _j = 175 °C		250		_
Qc	Total capacitive charge	$V_R = 400 V$			133		nC
С	Total capacitance	f = 1 MHz, V _R = 200 V			248		pF
		f = 1 MHz, V _R = 400) V		216		-
RthJC	Junction-to-case thermal resistance					0.86	°C/W



2.3 Performance Curves

This section shows the typical performance curves of the MSC2X51_50DC70J device.

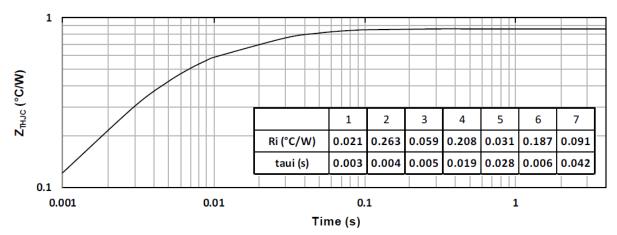
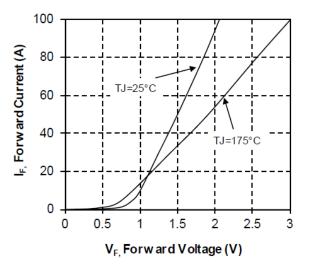
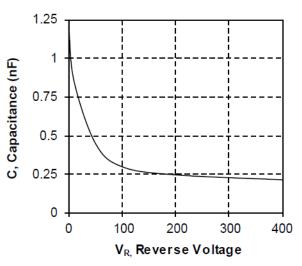


Figure 1 • Maximum Transient Thermal Impedance











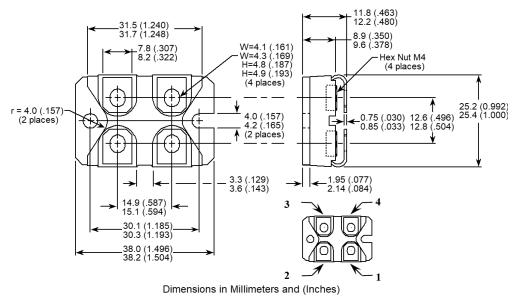
3 Package Specification

This section shows the package specification of the MSC2X51_50DC70J device.

3.1 Package Outline Drawing

The package outline of the MSC2X51_50DC70J device is illustrated in this section.

Figure 4 • Package Outline Drawing







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